Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4021	(planari?ation planari?e planari?ed planri?ing) near4 (semiconductor silicon)	US-PGPUB	OR	ON	2007/05/27 10:08
L2	12258	(planari?ation planari?e planari?ed planri?ing) near4 (semiconductor silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:08
L3	4511	(planari?ation planari?e planari?ed planari?ing) near1 (semiconductor silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:09
L4	0	(planari?ation planari?e planari?ed planari?ing) near1 (semiconductor silicon) and tft and el adj (layer film)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:09
L5	7	(planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and tft and el adj (layer film)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:10
L6	26	(planari?ation planari?e planari?ed planari?ing) near3 (semiconductor silicon) and tft and el adj (layer film)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:14
L7	446	(planari?ation planari?e planari?ed planari?ing) near3 (semiconductor silicon) and tft	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:14

L8	314	(planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and tft	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:35
L9	18	(planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and (257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) and @ad<"20031231"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:54
L10	0	"20010019133".pn. and common adj electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 10:55
L11	2	"20010019133".pn. and electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:15
L12	0	(semiconductor near1 energy).as. and optical adj print adj head.clm. and (EL adj (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:16
L13	0	optical adj print adj head.clm. and (EL adj (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:16
L14	2	optical adj print adj head.ti,ab,clm. and (EL adj (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:19

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L15	2	jp-2001167874$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 11:36
L16	2	("6841183").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:37
L17	2	("6841813").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:47
L18	18433	((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:52
L19	18676	((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911) or (257/e31.095) or (257/e31.096)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/27 11:52
L20	37	19 and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:01
L21	7	(fujiwara.in. sakuta.in. abiko.in. oki adj data.as. ogihara.in.) and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:11
L22	4	(fujiwara.in. sakuta.in. abiko.in. oki adj data.as. ogihara.in.) and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).clm. and compound adj semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:41

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L23	67	nakamura.in. and blue adj "LED"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:42
L24	9	nakamura.in. and blue adj "LED" and compound adj semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:43
L25	164	nakamura.in. and GaN and compound adj semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:45
L26	4	nakamura.in. and GaN and compound adj semiconductor and (planari?ing planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:46
L27	293	GaN and compound adj semiconductor and (planari?ing planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:53
L28	4	"651586".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:54
L29	4	"651586".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 12:54
S1	4	"743104".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 13:38
S2	1	(US-20040135157-$).did.	US-PGPUB	OR	OFF	2005/05/24 11:53
S3	0	jp-60206889$-$.did.	US-PGPUB	OR	OFF	2005/05/24 11:54
S4	1	jp-60206889$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58

S5	2	jp-10063807$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58
S6	152	(257/93).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S7	209	(257/501).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S8	360	S6 S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S9	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S10	1	S8 and (light adj emitting light-emitting) and (("without" "no") adj wire adj bond$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S11	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S12	34	S8 and (light adj emitting light-emitting) and planar$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S13	14	(US-6773943-$ or US-6692845-$ or US-6472718-$ or US-6403985-$ or US-6339233-$ or US-6114715-$ or US-5955747-$ or US-5866922-$ or US-5663581-$ or US-5115284-$ or US-4984035-$ or US-4956683-$ or US-4335501-$ or US-T979005-$).did.	USPAT	OR	OFF	2005/06/11 20:11
S14	4	S13 and print$3	US-PGPUB; USPAT	OR	OFF	2005/06/11 20:33
S15	5349	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40

EAST Search History

S16	1	S15 and monolithic and substrate near6 integrated adj circuit and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:39
S17	2	S15 and substrate near6 integrated adj circuit and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43
S18	0	S15 and monlithic and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43
S19	3	S15 and monolithic and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:45
S20	3	S15 and integrated adj circuit near6 substrate and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:46
S21	2	S15 and integrated adj circuit near6 (semiconductor silicon) near4 substrate and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:47
S22	2	S15 and (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:48
S23	17	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:55
S24	154	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz$5 and (LED light-emitting light adj emitting laser adj diode) and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:04

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S25	2	("5055907").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:26
S26	2	("4755866").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:30
S27	6922	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit$2 IC monolithic$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:31
S28	378	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit$2 IC monolithic$4) and planariz$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:38
S29	189	(light-emitting light adj emitting LED laser adj diode) adj array and (integrated adj circuit$2 IC monolithic$4) and planariz$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:22
S30	249	semi-insulating adj substrate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:23
S31	249	semi-insulating adj substrate.ti. and semi-insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:27
S32	3	semi-insulating adj substrate.ti. and semi-insulating near6 defined	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:33
S33	0	(silicon semiconductor semi-insulating) adj substrate near4 "having" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35
S34	0	(silicon semiconductor semi-insulating) adj substrate near4 "wherein" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35

S35	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near4 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S36	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near10 (driver integrated IC)	US-PGPUB; USPAT;. EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S37	1481	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S38	72	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) and planariz$5 and (LED light-emitting light adj emitting laser adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:51
S39	4756	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:52
S40	3231	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) and "257"/$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:53
S41	444	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:56
S42	317	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02
S43	54	(silicon semiconductor) adj substrate and thin adj2 film and planariz$5 adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02

S44		2	"5492851".pn. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:03
S45		2	"4902637".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 16:20
S46		0	(integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:11
S47		0	(integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:12
S48		79	(integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:22
S49		15	(US-20050087817-$ or US-20040155302-$ or US-20040155301-$ or US-20040016976-$ or US-20040012053-$ or US-20040007746-$ or US-20030067043-$).did. or (US-6903427-$ or US-6861715-$ or US-6812488-$ or US-6717222-$ or US-6706546-$ or US-6690845-$ or US-6684007-$ or US-6611635-$).did.	US-PGPUB; USPAT	OR	OFF	2005/06/12 15:22
S50	I	4	S49 and thin adj film near5 planariz$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:57
S51		0	S49 and thin adj film near5 planariz$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:25

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S52	4	S49 and thin adj film near5 planariz$5 and (IC adj layer integrated adj circuit adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:28
S53	4	S49 and thin adj film near5 planariz$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:45
S54	4	S49 and thin adj film near5 planariz$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:50
S55	0	S49 and thin adj film near5 planariz$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and vcsel adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:51
S56	4	S49 and thin adj film near5 planariz$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:52
S57	4	S49 and thin adj film near5 planariz$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer and (planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:53
S58	15	S49 and planariz$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58
S59	0	S49 and planariz$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58
S60	15	S49 and planariz$5 and (IC integrated adj circuit) adj2 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:58

S61	15	S49 and planariz$5 and (IC integrated adj circuit) adj2 layer and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00
S62	4	S49 and planariz$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00
S63	4	S49 and planariz$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S64	4	S49 and planariz$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall laser adj diode photodetect$3 photodiode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S65	15	IC adj layer near6 stack$3 and (planari?ation planari?e) and (EO LED light-emitting light adj emitting laser diode vcsel photodiode photodetect$3 hall adj sensor piezo-electric piezoelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:24
S66	29	cd-rom near4 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 18:37
S67	5991	memory adj device and memory adj cell adj array and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S68	2403	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S69	1206	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25

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S70	687	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S71	0	memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S72	0	memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:26
S73	0	memory adj device and memory adj cell adj array.ti,ab,clm. and (GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S74	0	memory adj device and memory adj cell adj array.ti,ab,clm. and (SiGe SiC GaAs AlGaAs) adj substrate.ti, ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S75	0	memory adj device and memory adj cell adj array and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S76	45	memory adj device and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab, clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:33
S77	5	memory adj device and (SiC) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S78	39	memory adj device and (GaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S79	12	config-dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:01

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S80	8	source near6 common adj ground and memory adj array.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:11
S81	31389	CD-ROM and Dvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:12
S82	2	CD-ROM and Dvd and memory adj array and laser adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
S83	2	"5696714".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
S84	5611	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40
S85	0	S84 and (planari?ation planari?e) and (Si silicon semiconductor) adj thin adj film and (integrated adj circuit IC) adj2 (layer) and (light-emitting light adj emitting laser adj diode photodiode photodetect$3 hall adj sensor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 20:42
S86	4649	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 15:59
S87	806	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:01

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S88	6	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:03
S89	2	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:04
S90	0	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminscent adj layer) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:05
S91	0	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminescent adj layer) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:05

S92	9	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and light-emitting and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:06
S93	12	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (light adj emitting light-emitting) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:06
S94	1614	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:07
S95	1097	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arseinde gallium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:08
S96	1098	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arseinde gallium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:08

S97	534	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:09
S98	287	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:10
S99	196	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:10
S100	15	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:13
S101	22	(planari?e planari?ed planari?ation planari?ing) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:16

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S10 2	32	(planari?e planari?ed planari?ation planari?ing planar) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing planar) near2 (film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:37
S10 3	13	(first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:41
S10 4	210	(first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:45
S10 5	62	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:47

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S10 6	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:48
S10 7	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:50
S10 8	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film otft silicon-on-insulator "soi")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:51
S10 9	14	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film otft silicon-on-insulator "soi")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 18:31

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S110	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:33
S111	19	"5492851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:34
S112	2	("5492851").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:34
S113	2	S112	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:42
S114	2	("20050199924").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:02
S115	2	("20050052823").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:13
S116	509	(257/752).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:38
S117	22	S116 and (thin adj film adj transistor tft otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:38
S118	22	S116 and (thin adj film adj transistor tft otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 19:40
S119	19	S116 and (thin adj film adj transistor tft otft) and (planar planari?e planari?ed planari?ation flat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 19:41

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S12 0	537	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:16
S12 1	0	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing) and intergated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:17
S12 2	184	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:18
S12 3	139	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 08:26
S12 4	1	(US-20040135157-$).did.	US-PGPUB	OR	OFF	2006/02/24 08:41
S12 5	1	S124 and raised adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:40
S12 6	0	zhang.in. and stacked near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:41
S12 7	0	semiconductor adj energy.in. and stacked near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:41
S12 8	0	semiconductor adj energy.in. and stack$3 near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42

S12 9	0	semiconductor adj energy.in. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42
S13 0	5688	semiconductor adj energy.as. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42
S13 1	21	semiconductor adj energy.as. and tft near4 stack$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:44
S13 2	457	tft near4 stack$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:44
S13 3	64	tft near4 stack$4.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 10:38
S13 4	28	tft near4 stack$4.ti,ab,clm. and (silicon semiconductor) near4 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 10:38
S13 5	1	(US-20040135157-$).did.	US-PGPUB	OR	OFF	2006/02/24 15:03
S13 6	9	optical adj print adj head and (tft active adj matrix adj display)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:07
S13 7	7	optical adj print adj head and (active adj matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S13 8	5	optical adj print adj head and (active adj matrix) and print adj head and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09

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S13 9	0	optical adj print adj head and (active adj matrix) and print adj head near20 tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S14 0	0	optical adj print adj head and (active adj matrix) and print adj head same tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S14 1	7	optical adj print adj head and (active adj matrix) and print adj head	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:12
S14 2	48	print adj head and ((active adj matrix) near20 tft) and print adj head	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:13
S14 3	1	print adj head and ((active adj matrix) near20 tft) near20 (print adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:14
S14 4	1	print$3 adj head and ((active adj matrix) near20 tft) near20 (print$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:16
S14 5	0	print$3 adj head and ((matrix adj2 display) near20 tft) near20 (print$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:16
S14 6	1	print$3 adj head and ((matrix) near20 tft) near20 (print$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28

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S14 7	0	09-045930$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28
S14 8	0	"09045930"$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28
S14 9	2	jp-09045930$-$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 19:43
S15 0	0	"6255705".pn. and print$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:41
S15 1	1	(US-20040135157-$).did.	US-PGPUB	OR	OFF	2006/02/24 17:21
S15 2	1	S151 and common	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:21
S15 3	1	S151 and common	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 17:21

S15 4	61	(US-20030141504-$ or US-20020163000-$ or US-20040135157-$ or US-20030067043-$ or US-20020168856-$ or US-20040012053-$ or US-20040007746-$ or US-20040130015-$ or US-20040094770-$ or US-20030102473-$ or US-20040125197-$ or US-20040166659-$ or US-20030170934-$ or US-20040089939-$ or US-20050100279-$ or US-20030133668-$ or US-20040155302-$ or US-20040155301-$ or US-20050087817-$ or US-20040016976-$ or US-20020061040-$).did. or (US-6828227-$ or US-5492851-$ or US-5031187-$ or US-6692837-$ or US-6476485-$ or US-6307264-$ or US-4902637-$ or US-6876008-$ or US-6773943-$ or US-6692845-$ or US-6472718-$ or US-6403985-$ or US-6339233-$ or US-6114715-$ or US-5955747-$ or US-5866922-$ or US-5663581-$ or US-5115284-$ or US-4984035-$ or US-4956683-$ or US-4335501-$ or US-T979005-$ or US-5055907-$ or US-5789766-$ or US-6410960-$ or US-6903427-$). did. or (US-6849877-$ or US-6861715-$ or US-6812488-$ or US-6717222-$ or US-6706546-$ or US-6690845-$ or US-6684007-$ or US-6611635-$ or US-6222755-$ or US-5696714-$ or US-6380572-$). did. or (JP-10063807-$ or JP-61102767-$).did. or (JP-10063807-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2006/02/24 17:24
S15 5	1	S154 and common near2 (source drain gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:25
S15 6	1	S154 and gate adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:04

S15 7	40	tft and active adj matrix and compound adj semiconductor near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:05
S15 8	18	tft and active adj matrix and compound adj semiconductor near1 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:15
S15 9	0	tft and active adj matrix and compound adj semiconductor near1 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:16
S16 0	0	tft and active adj matrix and (gan gaas compound adj semiconductor) near1 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:16
S16 1	14	tft and (gan gaas compound adj semiconductor) near5 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:17
S16 2	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 19:43
S16 3	7	"734294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 13:52
S16 4	2	("5838608").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:34
S16 5	19	"5492851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:34
S16 6	2	("5492851").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41

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S16 7	0	("743294.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41
S16 8	6	"743294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41
S16 9	7	"734294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:42
S17 0	2	"20040175887".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 15:28
S17 1	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 16:03
S17 2	8789	((257/79) or (257/93) or (257/88) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 16:04
S17 3	0	S172 and planarized adj (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06
S17 4	0	S172 and planarized near4 (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06
S17 5	1	S172 and planarized near4 (layer region film).ti,ab,clm. and (integrated adj circuit IC).ti,ab,clm. and (semiconductor silicon gan gaas sige) near2 substrate.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06

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S17 6	2	("6255705").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:03
S17 7	5	"384014".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:06
S17 8	2	("20040173808").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:06
S17 9	8	"561564"	DERWENT	OR	OFF	2006/12/08 20:07
S18 0	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/09 00:10
S18 1	1	(US-20040135157-$).did.	US-PGPUB	OR	OFF	2007/05/26 00:19
S18 2	1	(US-20040135157-$).did. and rough$4	US-PGPUB	OR	ON	2007/05/26 00:20
S18 3	2	("6255705").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 00:21
S18 4	1	(US-20040135157-$).did.	US-PGPUB	OR	OFF	2007/05/26 16:00
S18 6	1	(US-20040135157-$).did.	US-PGPUB	OR	OFF	2007/05/26 16:01
S18 7	1	S186 and rough$3	US-PGPUB	OR	OFF	2007/05/26 16:32
S18 8	1	S186 and rough$3 and thin adj2 film	US-PGPUB	OR	OFF	2007/05/26 16:49
S18 9	1	S186 and compound	US-PGPUB	OR	OFF	2007/05/26 16:49
S19 0	1	S186 and epitaxial$2 and thin and compound	US-PGPUB	OR	OFF	2007/05/26 17:16
S19 1	66	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm.	US-PGPUB	OR	ON	2007/05/26 17:19

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S19 2		22	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip). ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and "257"/$7.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:18
S19 3		22	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip). ti,ab,clm. and (light-emitting light adj emitting).ti,ab,clm. and "257"/$7.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:26
S19 4		22	S193 and (planari?ation planari?e planari?ed planari?ing) and (integrated adj circuit IC adj chip) and (light-emitting light adj emitting) and "257"/$7.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:24
S19 5		1	S193 and (planari?ation planari?e planari?ed planari?ing) and (integrated adj circuit IC adj chip) and (light-emitting light adj emitting) and "257"/$7.ccls. and monitoring adj device	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:25
S19 6		43	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip). ti,ab,clm. and (light-emitting light adj emitting) and "257"/$7.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:36
S19 7		4	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip). ti,ab,clm. and (light-emitting light adj emitting) and (257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:37
S19 8		13	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip). ti,ab,clm. and (light-emitting light adj emitting laser) and (257/79. ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/$7.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:41

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S19 9	72	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/$7.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:42
S20 0	38	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/$7.ccls.) and @ad<"20031225"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:48
S20 1	38	(planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/$7.ccls.) and @ad<"20031225" and (planari?ation planari?e planari?ed planari?ing)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 20:57
S20 2	2	("6734930").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 20:57
S20 3	1	"5504599".PN.	USPAT; USOCR	OR	OFF	2007/05/26 20:58
S20 4	1	"5796509".PN.	USPAT; USOCR	OR	OFF	2007/05/26 20:59
S20 5	1	"5926239".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:01
S20 6	1	"6194837".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:01
S20 7	1	"6441551".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:02
S20 8	1	"6441551".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:03
S20 9	1	"6556260".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:03

S21 0	1	"6628068".PN.	USPAT; USOCR	OR	OFF	2007/05/26 21:04
S21 1	1	"20020196387".PN.	US-PGPUB	OR	OFF	2007/05/26 21:04
S21 2	1	"20030063231".PN.	US-PGPUB	OR	OFF	2007/05/26 21:05
S21 3	1	"20030127656".PN.	US-PGPUB	OR	OFF	2007/05/26 21:22
S21 4	2	("5796509").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 21:23
S21 5	0	S214 and (planarized planarised planarize planarise planarization planarisation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/26 21:24
S21 6	2125	(planarized planarised planarize planarise planarization planarisation) and lcd and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:24
S21 7	738	(planarized planarised planarize planarise planarization planarisation) and (liquid adj crystal adj display lcd) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:26
S21 8	464	(planarized planarised planarize planarise planarization planarisation) and (liquid adj crystal adj display lcd) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab, clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:27
S21 9	53	(planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab,clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:45

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S22 0	717	(planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation)".ti,ab" and (planarized planarised planarize planarise planarization planarisation).clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:35
S22 1	4	(planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab. and (planarized planarised planarize planarise planarization planarisation).clm. and @ad<"20031231"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 21:35
S22 2	51	ppv near3 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:47
S22 3	70	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:49
S22 4	55	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:54
S22 5	0	(polyparaphenylene adj vinylene and polyvinyl adj carbazole and polyfluorane) near6 semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 22:53
S22 6	6	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor and electroluminescent	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/26 23:24
S22 7	6	(polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 (organic adj compound) and electroluminescent	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/27 00:30